

Title (en)
THIN FILM METALLIZATION AND BRAZING OF ALUMINUM NITRIDE.

Title (de)
DÜNNSCHICHTMETALLISIERUNG UND HARTLÖTEN VON ALUMINIUMNITRID.

Title (fr)
METALLISATION EN COUCHE MINCE ET BRASAGE DE NITRURE D'ALUMINIUM.

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Application
EP 93913864 A 19930512

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Abstract (en)
[origin: WO9323246A1] The aluminum nitride metallized structure (10) of the present invention includes a substrate (11) comprising an AlN sintered body and a metallized structure (21) formed on the substrate comprising a first layer (12) deposited on the sintered body and a second (B) layer deposited on the first layer (12). The first layer (12) comprises an alloy having the general formula (a) based on atomic percent: XxZ^{100-x} wherein X is at least one member selected from the group consisting of Ti, Zr, Hf and the rare earth elements, Z is at least one member selected from the group consisting of Mo, W, Cr, Nb, V and Ta, and $10 < x < 60$ atomic %. The second layer (13) comprises at least one member selected from the group consisting of Au, Co, Cu, Ni, and Fe.

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IPC 8 full level
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4. **C04B 41/009** + **C04B 35/581**

Citation (search report)
• [Y] CH 418214 A 19660731 - VARIAN ASSOCIATES [US]
• [A] PATENT ABSTRACTS OF JAPAN vol. 14, no. 304 (C - 734) 29 June 1990 (1990-06-29)
• See references of WO 9323246A1

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